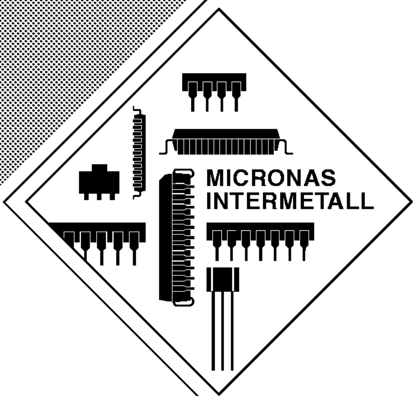

HAL525
Hall Effect Sensor IC

Edition March 10, 1999
6251-465-2DS

MICRONAS
INTERMETALL

Contents

Hall Effect Sensor Family
in CMOS technology

Release Notes: Revision bars indicate significant changes to the previous edition.

1. Introduction

The HAL525 is a Hall switch produced in CMOS technology. The sensor includes a temperature-compensated Hall plate with active offset compensation, a comparator, and an open-drain output transistor. The comparator compares the actual magnetic flux through the Hall plate (Hall voltage) with the fixed reference values (switching points). Accordingly, the output transistor is switched on or off.

The HAL525 has a latching behavior and requires a magnetic north and south pole for correct functioning. The output turns low with the magnetic south pole on the branded side of the package and turns high with the magnetic north pole on the branded side. The output does not change if the magnetic field is removed. For changing the output state, the opposite magnetic field polarity must be applied.

The active offset compensation leads to constant magnetic characteristics over supply voltage and temperature range. In addition, the magnetic parameters are robust against mechanical stress effects.

The sensor is designed for industrial and automotive applications and operates with supply voltages from 3.8 V to 24 V in the ambient temperature range from –40 °C up to 150 °C.

The HAL525 is available in an SMD-package (SOT-89A) and in a leaded version (TO-92UA). The introduction of the additional SMD-package SOT-89B is planned for 1999.

1.1. Features:

– switching offset compensation at typically 115 kHz

– typical B_{ON}: 14 mT at room temperature

– typical B_{OFF}: –14 mT at room temperature

– typical temperature coefficient of magnetic switching points is –2000 ppm/K

– operates from 3.8 V to 24 V supply voltage

– overvoltage protection at all pins

– reverse-voltage protection at V_{DD}-pin

– magnetic characteristics are robust against mechanical stress effects

– short-circuit protected open-drain output by thermal shut down

– operates with static magnetic fields and dynamic magnetic fields up to 10 kHz

– on-chip temperature compensation circuitry minimizes shifts of magnetic characteristics over temperature

– constant switching points over a wide supply voltage range

– the decrease of magnetic flux density caused by rising temperature in the sensor system is compensated by a built-in negative temperature coefficient of the magnetic characteristics

– ideal sensor for window lifter, ignition timing, and revolution counting in extreme automotive and industrial environments

– EMC corresponding to DIN 40839

1.2. Marking Code

All Hall sensors have a marking on the package surface (branded side). This marking includes the name of the sensor and the temperature range.

Type	Temperature Range			
	A	K	E	C
HAL525	525A	525K	525E	525C

1.3. Operating Junction Temperature Range

A: T_J = –40 °C to +170 °C

K: T_J = –40 °C to +140 °C

E: T_J = –40 °C to +100 °C

C: T_J = 0 °C to +100 °C

The Hall sensors from MICRONAS INTERMETALL are specified to the chip temperature (junction temperature T_J).

The relationship between ambient temperature (T_A) and junction temperature is explained in section 4.1. on page 14.

1.4. Hall Sensor Package Codes

HAL XXXPA-T

- Temperature Range: A, K, E, or C
- Package: SF for SOT-89B
  SO for SOT-89A
  UA for TO-92UA
- Type: 525

Example: **HAL 525UA-E**

→ Type: 525
→ Package: TO-92UA
→ Temperature Range: T_J = –40 °C to +100 °C

Hall sensors are available in a wide variety of packaging versions and quantities. For more detailed information, please refer to the brochure: "Ordering Codes for Hall Sensors".

1.5. Solderability

all packages: according to IEC68-2-58

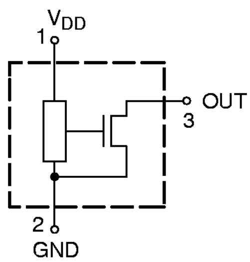

Fig. 1–1: Pin configuration

2. Functional Description

The Hall effect sensor is a monolithic integrated circuit that switches in response to magnetic fields. If a magnetic field with flux lines perpendicular to the sensitive area is applied to the sensor, the biased Hall plate forces a Hall voltage proportional to this field. The Hall voltage is compared with the actual threshold level in the comparator. The temperature-dependent bias increases the supply voltage of the Hall plates and adjusts the switching points to the decreasing induction of magnets at higher temperatures. If the magnetic field exceeds the threshold levels, the open drain output switches to the appropriate state. The built-in hysteresis eliminates oscillation and provides switching behavior of output without bouncing.

Magnetic offset caused by mechanical stress is compensated for by using the "switching offset compensation technique". Therefore, an internal oscillator provides a two phase clock. The Hall voltage is sampled at the end of the first phase. At the end of the second phase, both sampled and actual Hall voltages are averaged and compared with the actual switching point. Subsequently, the open drain output switches to the appropriate state. The time from crossing the magnetic switching level to switching of output can vary between zero and $1/f_{osc}$.

Shunt protection devices clamp voltage peaks at the Output-pin and V_{DD}-pin together with external series resistors. Reverse current is limited at the V_{DD}-pin by an internal series resistor up to –15 V. No external reverse protection diode is needed at the V_{DD}-pin for reverse voltages ranging from 0 V to –15 V.

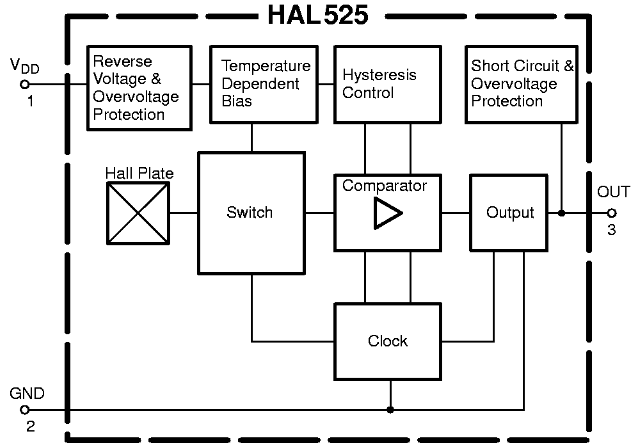

Fig. 2–1: HAL525 block diagram

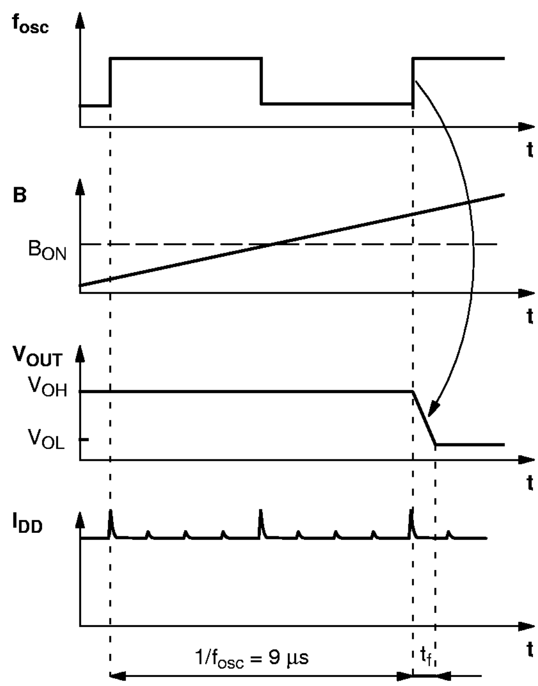

Fig. 2–2: Timing diagram

3. Specifications

3.1. Outline Dimensions

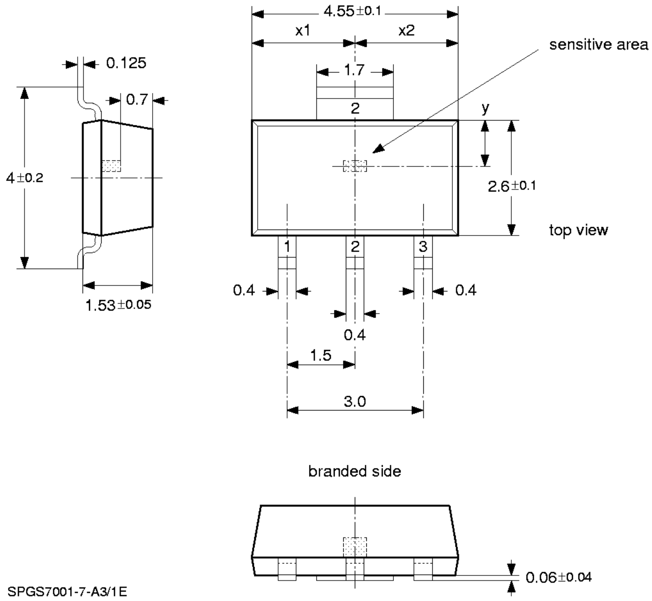

Fig. 3–1:
Plastic Small Outline Transistor Package
(SOT-89A)
Weight approximately 0.04 g
Dimensions in mm

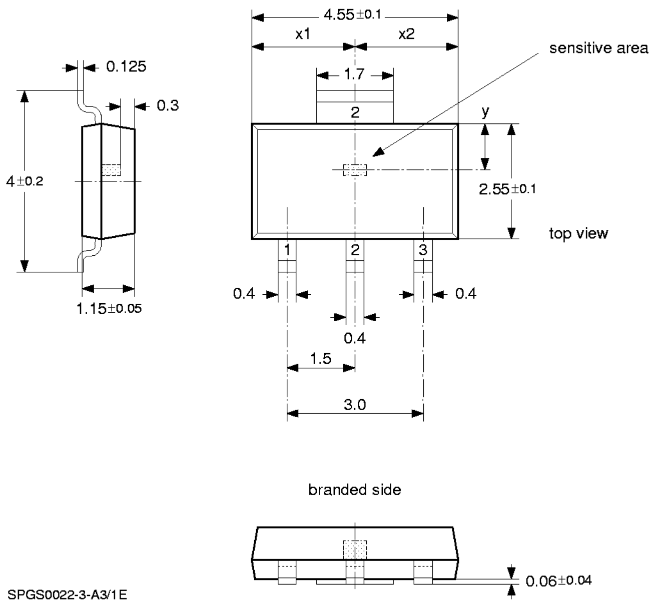

Fig. 3–2:
Plastic Small Outline Transistor Package
(SOT-89B)
Weight approximately 0.035 g
Dimensions in mm

Note: This package will be introduced in 1999. Samples are available. Contact the sales offices for high volume delivery.

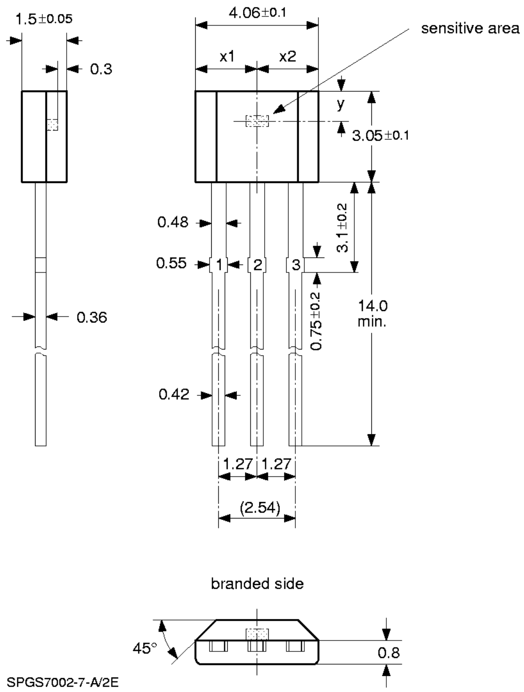

Fig. 3–3:
Plastic Transistor Single Outline Package
(TO-92UA)
Weight approximately 0.12 g
Dimensions in mm

For all package diagrams, a mechanical tolerance of ±50 µm applies to all dimensions where no tolerance is explicitly given.

3.2. Dimensions of Sensitive Area

0.25 mm x 0.12 mm

3.3. Positions of Sensitive Areas

SOT-89A	SOT-89B	TO-92UA
$\lvert x_2 - x_1 \rvert / 2 < 0.2$ mm		
y = 0.98 mm ± 0.2 mm	y = 0.95 mm ± 0.2 mm	y = 1.0 mm ± 0.2 mm

3.4. Absolute Maximum Ratings

Symbol	Parameter	Pin No.	Min.	Max.	Unit
V_{DD}	Supply Voltage	1	–15	28[1)]	V
$-V_P$	Test Voltage for Supply	1	–24[2)]	–	V
$-I_{DD}$	Reverse Supply Current	1	–	50[1)]	mA
I_{DDZ}	Supply Current through Protection Device	1	–200[3)]	200[3)]	mA
V_O	Output Voltage	3	–0.3	28[1)]	V
I_O	Continuous Output On Current	3	–	50[1)]	mA
I_{Omax}	Peak Output On Current	3	–	250[3)]	mA
I_{OZ}	Output Current through Protection Device	3	–200[3)]	200[3)]	mA
T_S	Storage Temperature Range		–65	150	°C
T_J	Junction Temperature Range		–40 –40	150 170[4)]	°C

[1)] as long as $T_J$max is not exceeded
[2)] with a 220 Ω series resistance at pin 1 corresponding to test circuit 1
[3)] t<2 ms
[4)] t<1000h

Stresses beyond those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only. Functional operation of the device at these or any other conditions beyond those indicated in the "Recommended Operating Conditions/Characteristics" of this specification is not implied. Exposure to absolute maximum ratings conditions for extended periods may affect device reliability.

3.5. Recommended Operating Conditions

Symbol	Parameter	Pin No.	Min.	Max.	Unit
V_{DD}	Supply Voltage	1	3.8	24	V
I_O	Continuous Output On Current	3	0	20	mA
V_O	Output Voltage (output switched off)	3	0	24	V

3.6. Electrical Characteristics at T_J = –40 °C to +170 °C , V_{DD} = 3.8 V to 24 V, as not otherwise specified in Conditions
Typical Characteristics for T_J = 25 °C and V_{DD} = 12 V

Symbol	Parameter	Pin No.	Min.	Typ.	Max.	Unit	Conditions
I_{DD}	Supply Current	1	2.3	3	4.2	mA	T_J = 25 °C
I_{DD}	Supply Current over Temperature Range	1	1.6	3	5.2	mA	
V_{DDZ}	Overvoltage Protection at Supply	1	–	28.5	32	V	I_{DD} = 25 mA, T_J = 25 °C, t = 20 ms
V_{OZ}	Overvoltage Protection at Output	3	–	28	32	V	I_{OH} = 25 mA, T_J = 25 °C, t = 20 ms
V_{OL}	Output Voltage	3	–	130	280	mV	I_{OL} = 20 mA, T_J = 25 °C
V_{OL}	Output Voltage over Temperature Range	3	–	130	400	mV	I_{OL} = 20 mA
I_{OH}	Output Leakage Current	3	–	0.06	0.1	µA	Output switched off, T_J = 25 °C, V_{OH} = 3.8 to 24 V
I_{OH}	Output Leakage Current over Temperature Range	3	–	–	10	µA	Output switched off, $T_J \leq 150$ °C, V_{OH} = 3.8 to 24 V
f_{osc}	Internal Oscillator Chopper Frequency	–	95	115	–	kHz	T_J = 25 °C,
f_{osc}	Internal Oscillator Chopper Frequency over Temperature Range	–	85	115	–	kHz	T_J = –30 °C to 100 °C
f_{osc}	Internal Oscillator Chopper Frequency over Temperature Range	–	73	115	–	kHz	
$t_{en(O)}$	Enable Time of Output after Setting of V_{DD}	1	–	30	70	µs	V_{DD} = 12 V $B > B_{ON}$ + 2 mT or $B < B_{OFF}$ – 2 mT
t_r	Output Rise Time	3	–	75	400	ns	V_{DD} = 12 V, R_L = 820 Ohm, C_L = 20 pF
t_f	Output Fall Time	3	–	50	400	ns	
R_{thJSB} case SOT-89A SOT-89B	Thermal Resistance Junction to Substrate Backside	–	–	150	200	K/W	Fiberglass Substrate 30 mm x 10 mm x 1.5mm, pad size see Fig. 3–4
R_{thJA} case TO-92UA	Thermal Resistance Junction to Soldering Point	–	–	150	200	K/W	

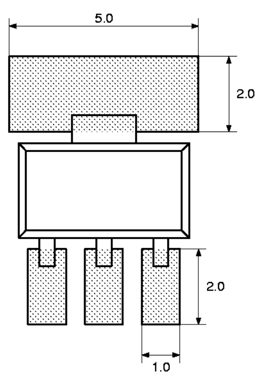

Fig. 3–4: Recommended pad size SOT-89x
Dimensions in mm

3.7. Magnetic Characteristics at T_J = –40 °C to +170 °C, V_{DD} = 3.8 V to 24 V,
Typical Characteristics for V_{DD} = 12 V

Magnetic flux density values of switching points.
Positive flux density values refer to the magnetic south pole at the branded side of the package.

Parameter	On point B_{ON}			Off point B_{OFF}			Hysteresis B_{HYS}			Magnetic Offset			Unit
T_J	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	
–40 °C	11.8	15.8	19.2	–19.2	–15.8	–11.8	27.4	31.6	35.8		0		mT
25 °C	11	14	17	–17	–14	–11	24	28	32	–2	0	2	mT
100 °C	8	11	15.5	–15.5	–11	–8	18.5	22	28.7		0		mT
140 °C	6.5	10	14	–14	–10	–6.5	16	20	26		0		mT
170 °C	5	8.5	13	–13	–8.5	–5	12	17	25		0		mT

The hysteresis is the difference between the switching points $B_{HYS} = B_{ON} - B_{OFF}$
The magnetic offset is the mean value of the switching points $B_{OFFSET} = (B_{ON} + B_{OFF}) / 2$

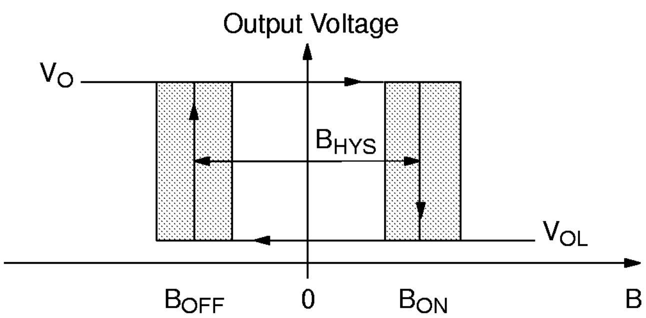

Fig. 3–5: Definition of magnetic switching points

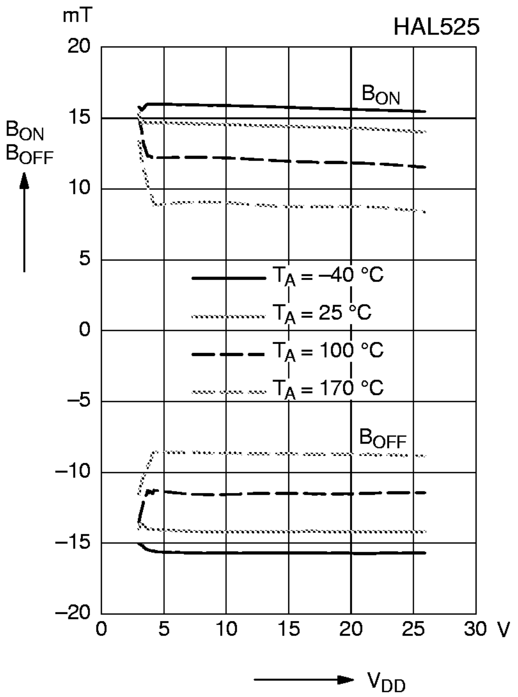

Fig. 3–6: Typical magnetic switching points versus supply voltage

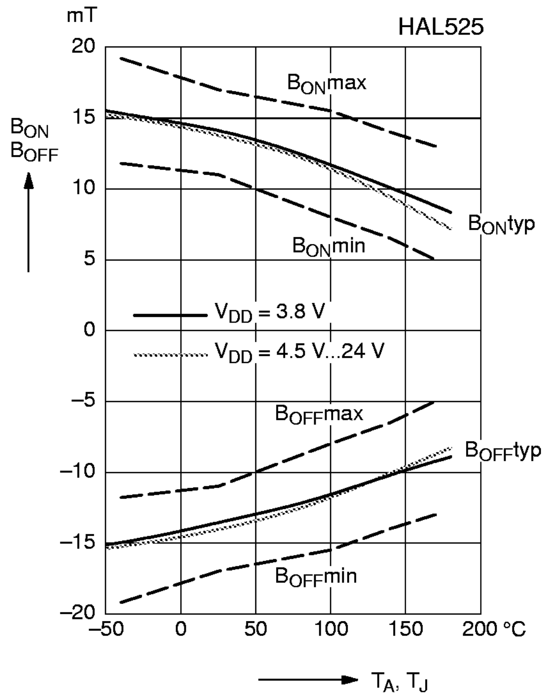

Fig. 3–8: Magnetic switching points versus temperature

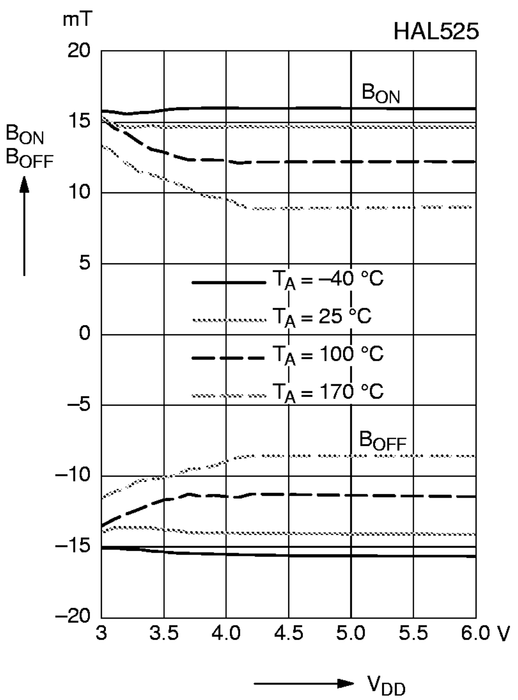

Fig. 3–7: Typical magnetic switching points versus supply voltage

Note: In the diagram “Typical magnetic switching points versus ambient temperature” the curves for B_{ON}min, B_{ON}max, B_{OFF}min, and B_{OFF}max refer to junction temperature, whereas typical curves refer to ambient temperature.

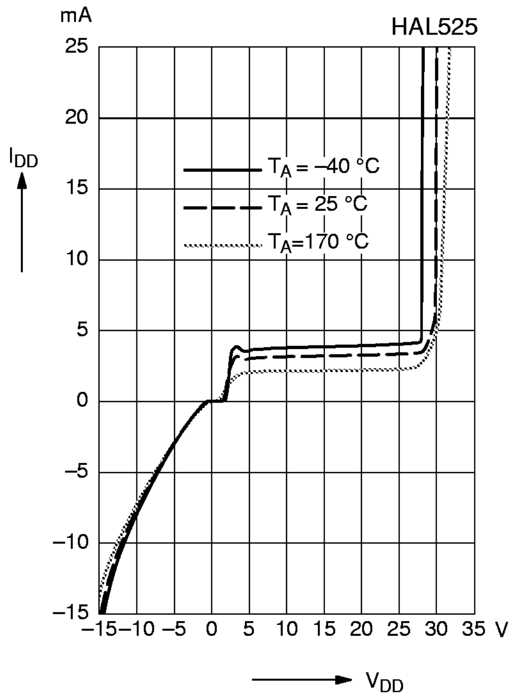

Fig. 3–9: Typical supply current versus supply voltage

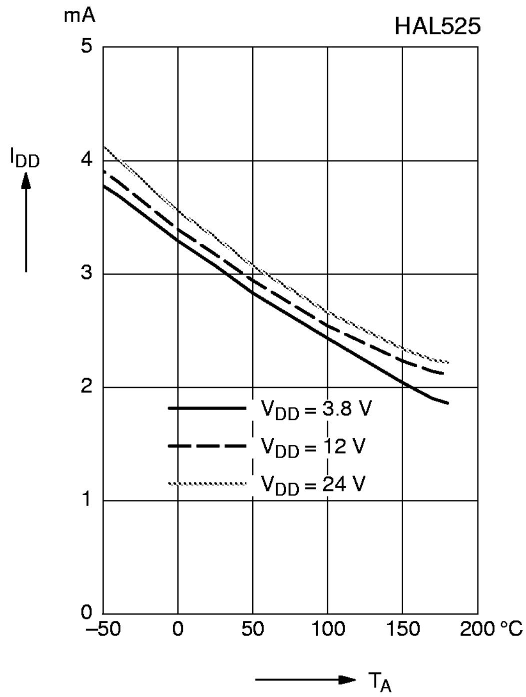

Fig. 3–11: Typical supply current versus ambient temperature

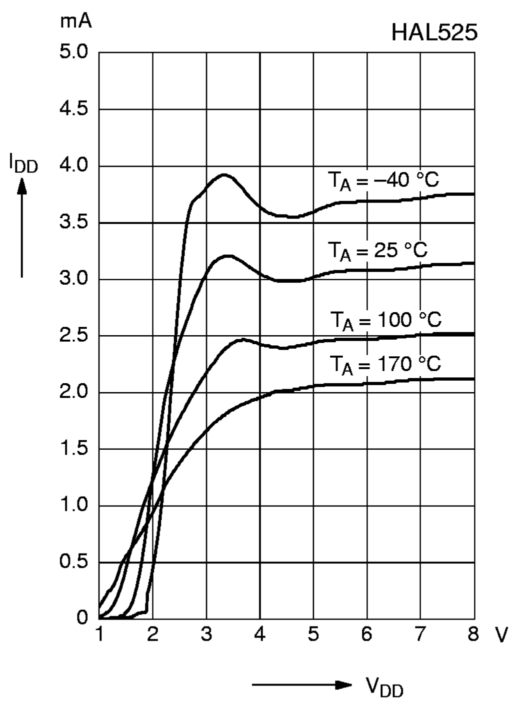

Fig. 3–10: Typical supply current versus supply voltage

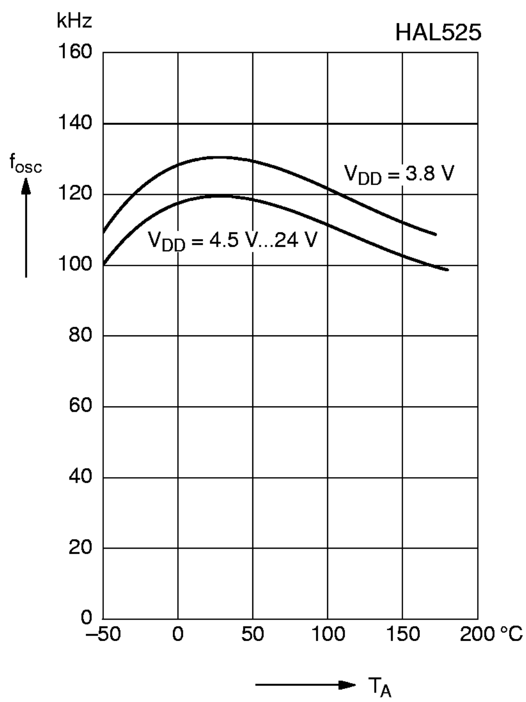

Fig. 3–12: Typ. internal chopper frequency versus ambient temperature

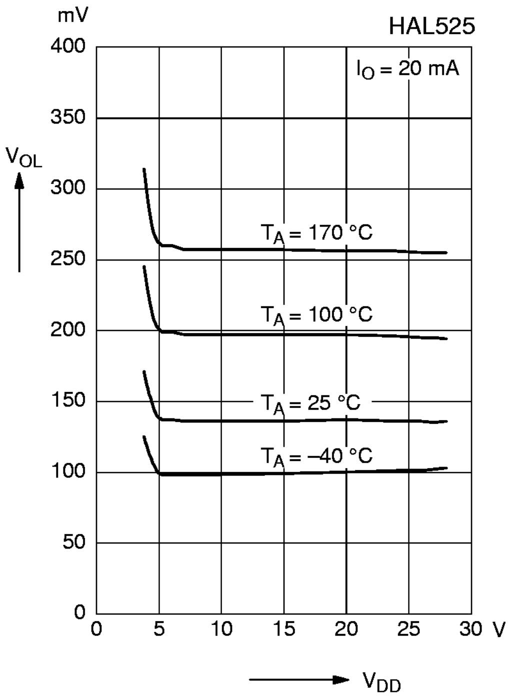

Fig. 3–13: Typical output low voltage versus supply voltage

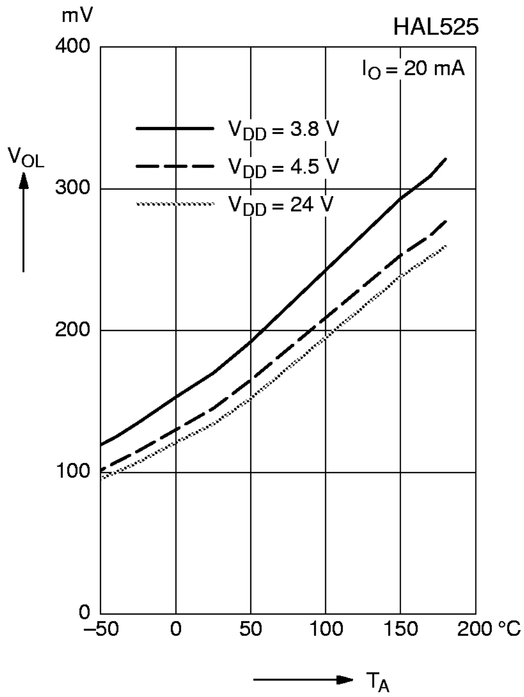

Fig. 3–15: Typical output low voltage versus ambient temperature

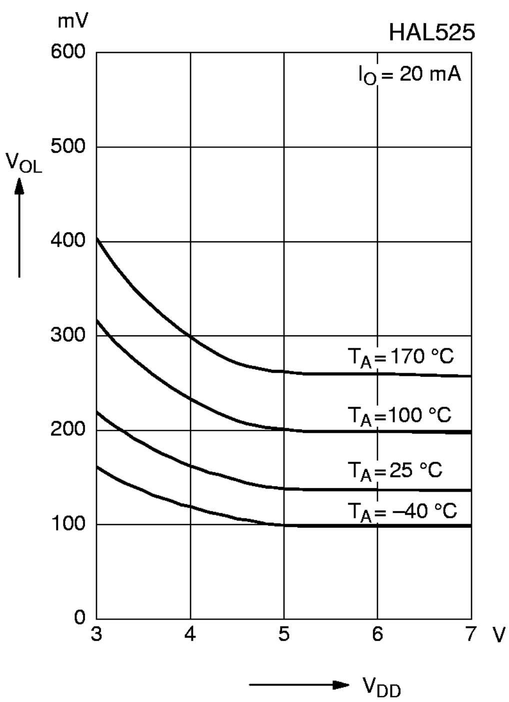

Fig. 3–14: Typical output low voltage versus supply voltage

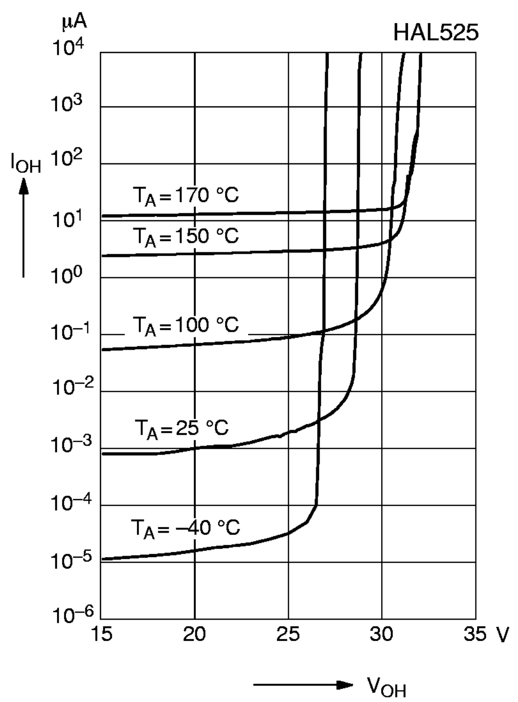

Fig. 3–16: Typical output high current versus output voltage

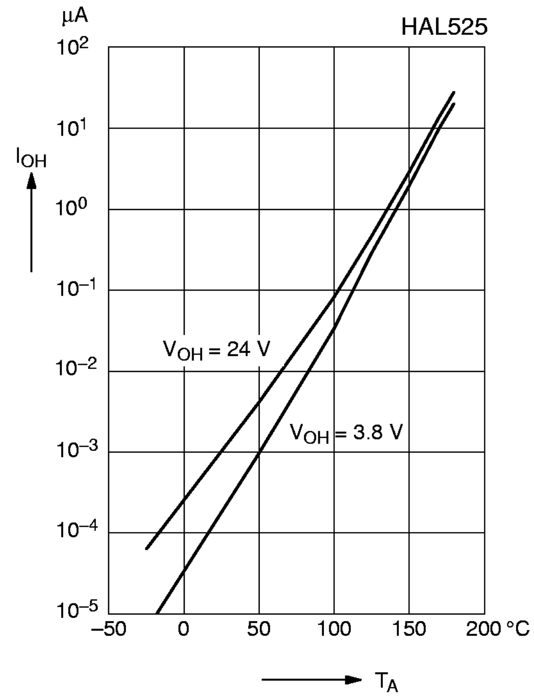

Fig. 3–17: Typical output leakage current versus ambient temperature

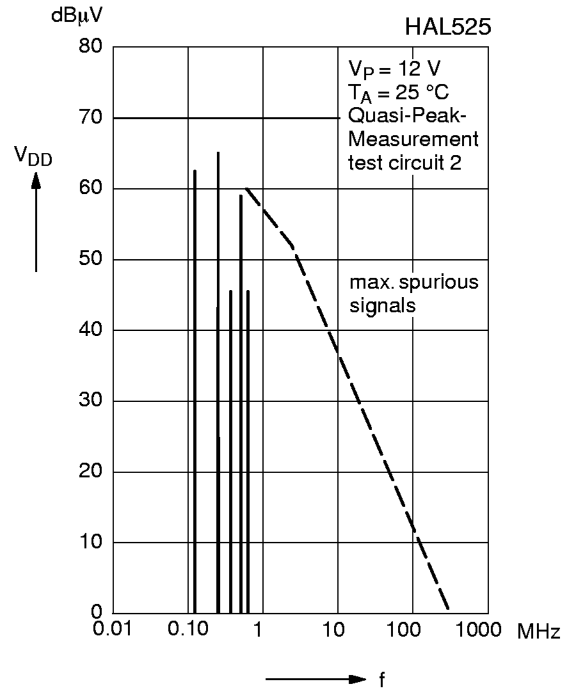

Fig. 3–19: Typ. spectrum of supply voltage

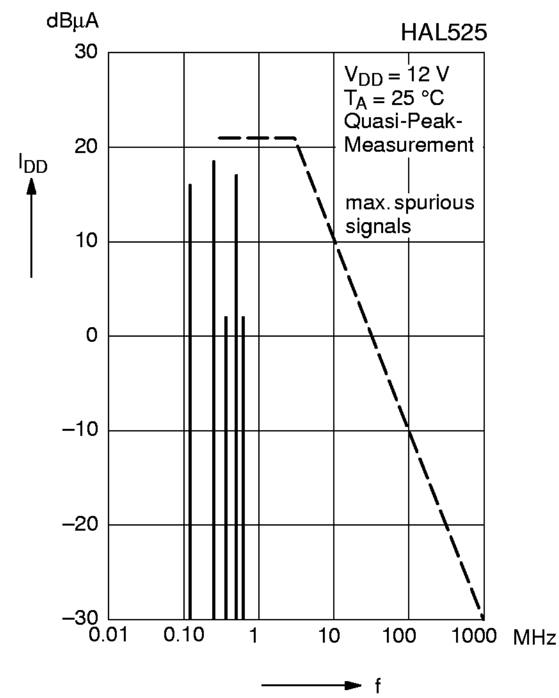

Fig. 3–18: Typ. spectrum of supply current

4. Application Notes

4.1. Ambient Temperature

Due to the internal power dissipation, the temperature on the silicon chip (junction temperature T_J) is higher than the temperature outside the package (ambient temperature T_A).

$T_J = T_A + \Delta T$

At static conditions, the following equation is valid:

$\Delta T = I_{DD} * V_{DD} * R_{th}$

For typical values, use the typical parameters. For worst case calculation, use the max. parameters for I_{DD} and R_{th}, and the max. value for V_{DD} from the application.

For all sensors, the junction temperature range T_J is specified. The maximum ambient temperature T_{Amax} can be calculated as:

$T_{Amax} = T_{Jmax} - \Delta T$

4.2. Extended Operating Conditions

All sensors fulfill the electrical and magnetic characteristics when operated within the Recommended Operating Conditions (see page 7).

Supply Voltage Below 3.8 V

Typically, the sensors operate with supply voltages above 3 V, however, below 3.8 V some characteristics may be outside the specification.

Note: The functionality of the sensor below 3.8 V has not been tested. For special test conditions, please contact MICRONAS INTERMETALL.

4.3. Start-up Behavior

Due to the active offset compensation, the sensors have an initialization time (enable time $t_{en(O)}$) after applying the supply voltage. The parameter $t_{en(O)}$ is specified in the Electrical Characteristics (see page 8).

During the initialization time, the output state is not defined and the output can toggle. After $t_{en(O)}$, the output will be low if the applied magnetic field B is above B_{ON}. The output will be high if B is below B_{OFF}.

For magnetic fields between B_{OFF} and B_{ON}, the output state of the HAL sensor after applying V_{DD} will be either low or high. In order to achieve a well-defined output state, the applied magnetic field must be above B_{ONmax}, respectively, below B_{OFFmin}.

4.4. EMC

For applications with disturbances on the supply line or radiated disturbances, a series resistor and a capacitor are recommended (see figures 4–1 and 4–2).

The series resistor and the capacitor should be placed as closely as possible to the HAL sensor.

The EMC performance has been tested in a lab environment with EMC optimized printed circuit board layouts. The results in the following tables show that function classes A and C could be reached in these investigations. Depending on customer circuit designs and layouts, EMC results obtained in those applications may be different from the ones obtained in the MICRONAS INTERMETALL lab investigations.

Test Circuits for Electromagnetic Compatibility
Test pulses V_{EMC} corresponding to DIN 40839.

Note: The international standard ISO 7637 is similar to the used product standard DIN 40839.

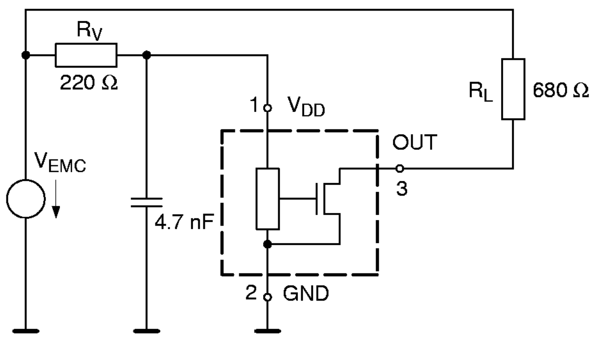

Fig. 4–1: Test circuit 1

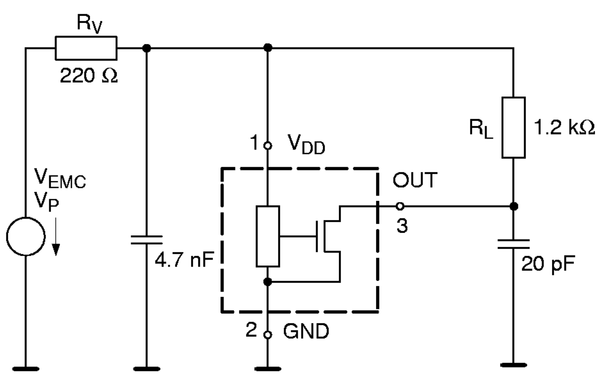

Fig. 4–2: Test circuit 2

Interferences conducted along supply lines in 12 V onboard systems

Product standard: DIN 40839 part 1

Test-Pulse	Severity Level	U_S in V	Test circuit	Pulses/Time	Function Class	Remarks
1	IV	–100	1	5000	C	5 s pulse interval
2	IV	100	1	5000	C	0.5 s pulse interval
3a	IV	–150	2	1 h	A	
3b	IV	100	2	1 h	A	
4	IV	–7	2	5	A	
5	IV	86.5	1	10	C	10 s pulse interval

Electrical transient transmission by capacitive and inductive coupling via lines other than the supply lines

Product standard: DIN 40839 part 3

Test-Pulse	Severity Level	U_S in V	Test circuit	Pulses/Time	Function Class	Remarks
1	IV	–30	2	500	A	5 s pulse interval
2	IV	30	2	500	A	0.5 s pulse interval
3a	IV	–60	2	10 min	A	
3b	IV	40	2	10 min	A	

Radiated Disturbances

Product standard: DIN 40839 part 4

Test Conditions

– Temperature: Room temperature (22...25 °C)

– Supply voltage: 13 V

– Lab Equipment: TEM cell 220 MHz
with adaptor board 455 mm, device 80 mm over ground

– Frequency range: 5...220 MHz; 1 MHz steps

– Test circuit 2

– tested with static magnetic fields

Tested Devices and Results

Type	Field Strength during test	Modulation	Result
HAL525	> 200 V/m	–	output voltage stable on the level high or low[1)]
HAL525	> 200 V/m	1 kHz 80 %	output voltage stable on the level high or low[1)]
[1)] low level < 0.4 V, high level > 90% of V_{DD}			

5. Data Sheet History

1. Final data sheet: “HAL 525 Hall Effect Sensor IC”, April 23, 1997, 6251-465-1DS. First release of the final data sheet.
2. Final data sheet: “HAL 525 Hall Effect Sensor IC”, March 10, 1999, 6251-465-2DS. Second release of the final data sheet. Major changes:

- additional package SOT-89B
- outline dimensions for SOT-89A and TO-92UA changed
- electrical characteristics changed
- section 4.2.: Extended Operating Conditions added
- section 4.3.: Start-up Behavior added

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